

MMBTA13L, SMMBTA13L, MMBTA14L, SMMBTA14L

Darlington Amplifier Transistors

NPN Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--------------------------------|-----------|-------|------|
| Collector - Emitter Voltage | V_{CES} | 30 | Vdc |
| Collector - Base Voltage | V_{CBO} | 30 | Vdc |
| Emitter - Base Voltage | V_{EBO} | 10 | Vdc |
| Collector Current - Continuous | I_C | 300 | mA |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---------------------------------------------------------------------------------------------------------------------|-----------------|-------------|----------------------------|
| Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 225 1.8 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 556 | $^\circ\text{C}/\text{W}$ |
| Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 300 2.4 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 417 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

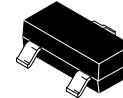
1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

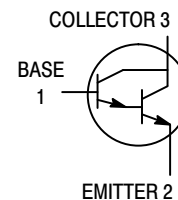


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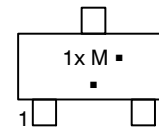
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SOT-23 (TO-236)
CASE 318
STYLE 6



MARKING DIAGRAM



- 1x = Device Code
 x = M for MMBTA13LT1G,
 SMMBTA13LT1G
 x = N for MMBTA14LT1G,
 SMMBTA14LT1G, T3G
 M = Date Code*
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping† |
|------------------------------|---------------------|----------------------|
| MMBTA13LT1G, SMMBTA13LT1G | SOT-23 (Pb-Free) | 3,000 / Tape & Reel |
| MMBTA14LT1G, SMMBTA14LT1G | SOT-23 (Pb-Free) | 3,000 / Tape & Reel |
| SMMBTA14LT3G | SOT-23 (Pb-Free) | 10,000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBTA13L, SMMBTA13L, MMBTA14L, SMMBTA14L

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|---------------------------------------------------------------------------------------|---------------|-----|-----|------|
| OFF CHARACTERISTICS | | | | |
| Collector – Emitter Breakdown Voltage ($I_C = 100 \mu\text{Adc}$, $V_{BE} = 0$) | $V_{(BR)CES}$ | 30 | – | Vdc |
| Collector Cutoff Current ($V_{CB} = 30 \text{ Vdc}$, $I_E = 0$) | I_{CBO} | – | 100 | nAdc |
| Emitter Cutoff Current ($V_{EB} = 10 \text{ Vdc}$, $I_C = 0$) | I_{EBO} | – | 100 | nAdc |

ON CHARACTERISTICS (Note 3)

| | | | | |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|------------------------------------|------------------|-----|
| DC Current Gain ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$) MMBTA13, SMMBTA13 MMBTA14, SMMBTA14 ($I_C = 100 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$) MMBTA13, SMMBTA13 MMBTA14, SMMBTA14 | h_{FE} | 5000 10,000 10,000 20,000 | – – – – | – |
| Collector – Emitter Saturation Voltage ($I_C = 100 \text{ mAdc}$, $I_B = 0.1 \text{ mAdc}$) | $V_{CE(sat)}$ | – | 1.5 | Vdc |
| Base – Emitter On Voltage ($I_C = 100 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$) | V_{BE} | – | 2.0 | Vdc |

SMALL-SIGNAL CHARACTERISTICS

| | | | | |
|---------------------------------------------------------------------------------------------------------------------------------|-------|-----|---|-----|
| Current – Gain – Bandwidth Product (Note 4) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 100 \text{ MHz}$) | f_T | 125 | – | MHz |
|---------------------------------------------------------------------------------------------------------------------------------|-------|-----|---|-----|

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

4. $f_T = |h_{fe}| \cdot f_{test}$.



Figure 1. Transistor Noise Model

MMBTA13L, SMMBTA13L, MMBTA14L, SMMBTA14L

NOISE CHARACTERISTICS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)



Figure 2. Noise Voltage

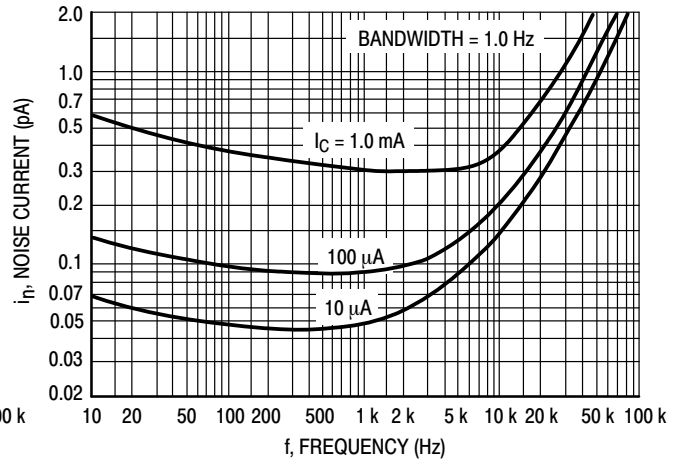


Figure 3. Noise Current

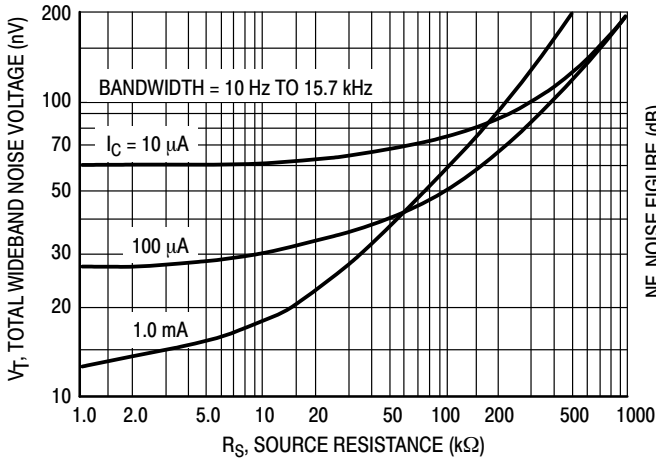


Figure 4. Total Wideband Noise Voltage

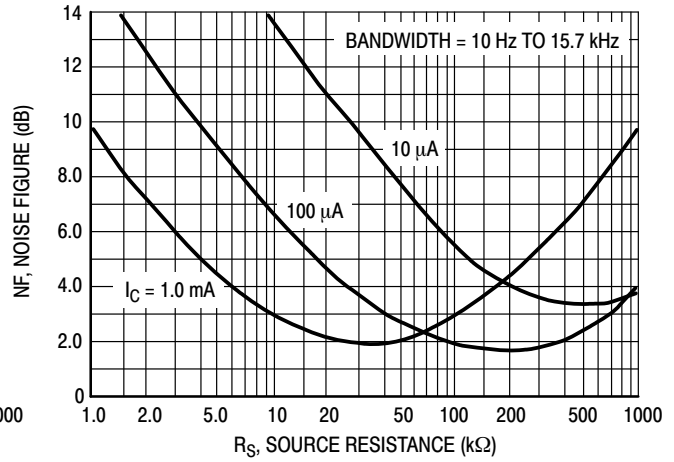


Figure 5. Wideband Noise Figure

SMALL-SIGNAL CHARACTERISTICS

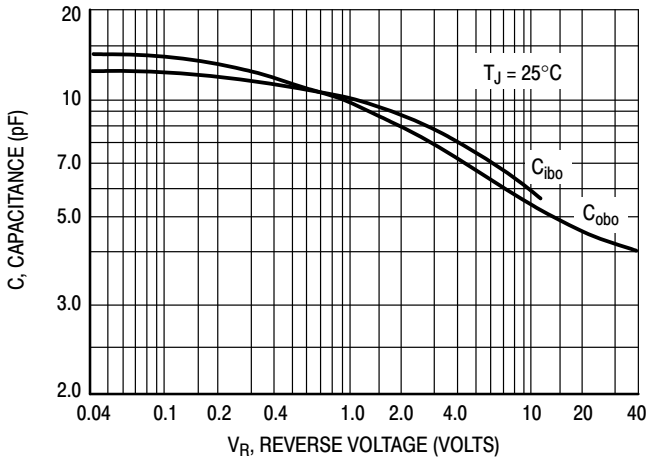


Figure 6. Capacitance

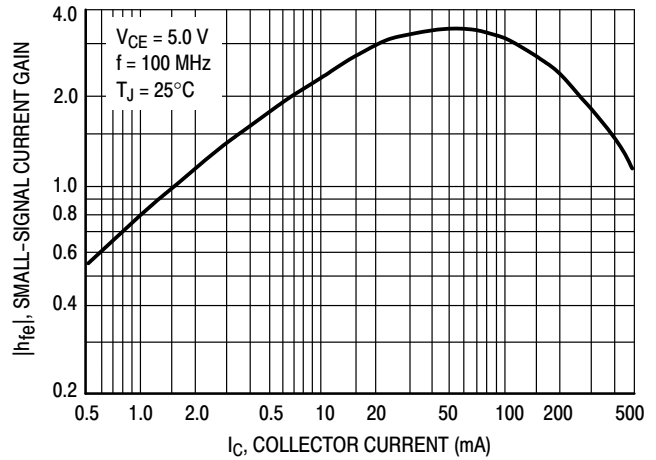


Figure 7. High Frequency Current Gain

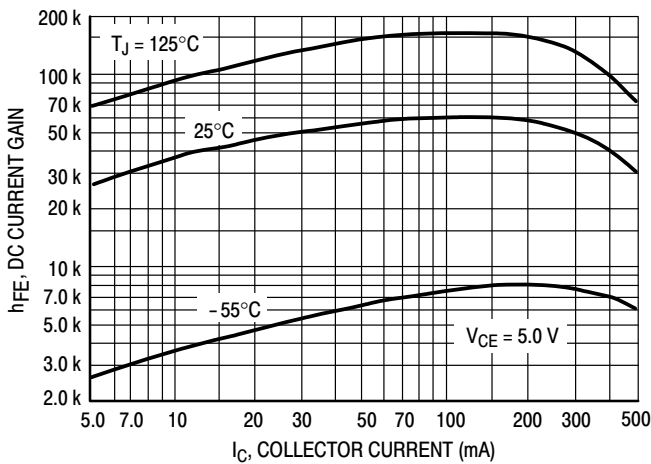


Figure 8. DC Current Gain

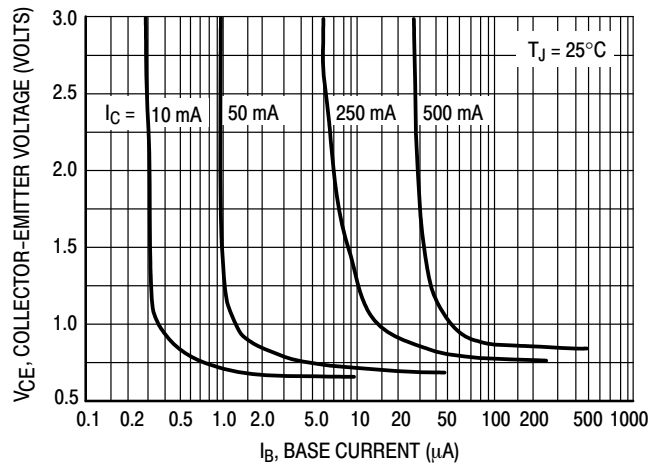


Figure 9. Collector Saturation Region

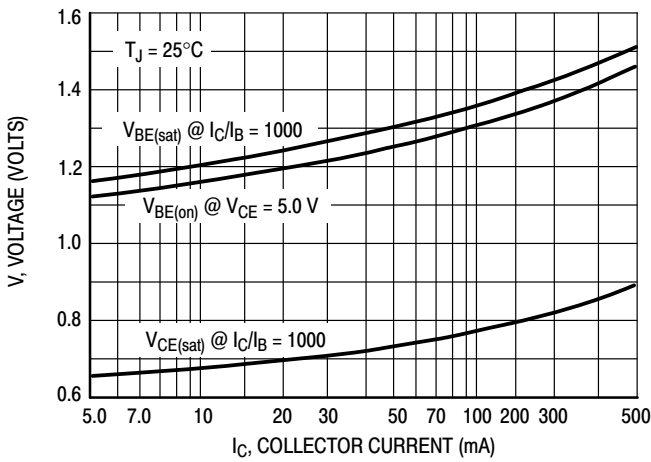


Figure 10. "On" Voltages

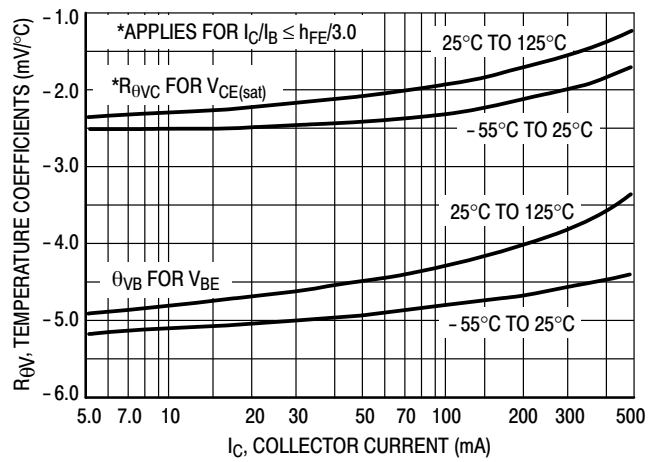


Figure 11. Temperature Coefficients

MMBTA13L, SMMBTA13L, MMBTA14L, SMMBTA14L



Figure 12. Thermal Response



Figure 13. Active Region Safe Operating Area

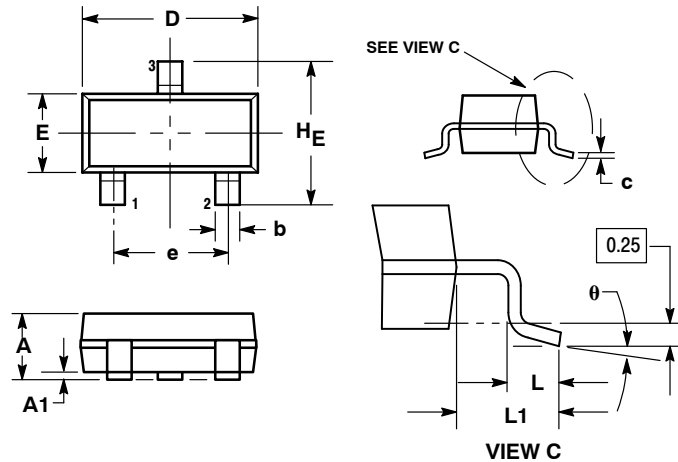


Design Note: Use of Transient Thermal Resistance Data

MMBTA13L, SMMBTA13L, MMBTA14L, SMMBTA14L

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AP



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|--------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.89 | 1.00 | 1.11 | 0.035 | 0.040 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.001 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.018 | 0.020 |
| c | 0.09 | 0.13 | 0.18 | 0.003 | 0.005 | 0.007 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.081 |
| L | 0.10 | 0.20 | 0.30 | 0.004 | 0.008 | 0.012 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.029 |
| HE | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| θ | 0° | --- | 10° | 0° | --- | 10° |

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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